MSKSEMI 美森科













ESD

TVS

TSS

MOV

GDI

PIFD

LM317

Product specification





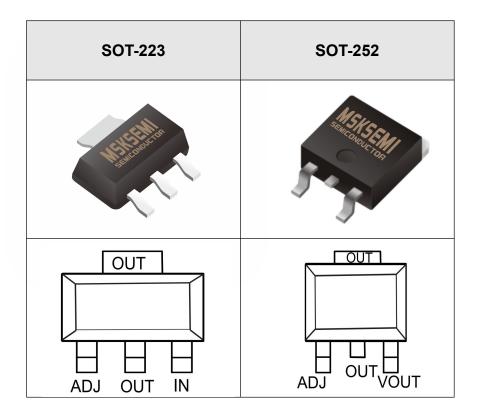
DESCRIPTION

This monolithic integrated circuit is an adjustable 3-terminal positive voltage regulator designed to supply more than 1.5A of load current with an output voltage adjustable over a 1.2 to 37V.It employs internal current limiting, thermal shut-down and safe area compensation.

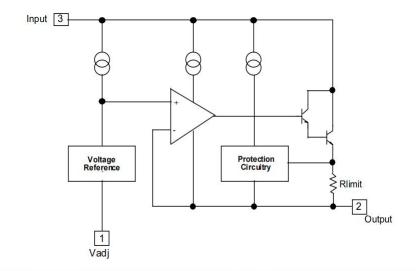
FEATURE

- Internal thermal overload protection
- Internal short circuit current limiting
- Output transistor safe operating area compensation

Reference News



Internal Block Diagram





Absolute Maximum Ratings

Symbol	Parameter	Value	Units	
V _I -V _O	Input-Output Voltage Differential	40	V	
TLEAD	Lead Temperature	230	$^{\circ}$	
P_D	Power Dissipation Internally lim		W	
TJ	Operating Junction Temperature Range	0~125		
T _{stg}	Storage Temperature Range	-55~125	°C	
ΔV _O /ΔΤ	Temperature Coefficient of Output Voltage ±0.02			

ELECTRICAL CHARACTERISTICS

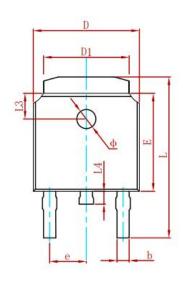
(VO-VI=5V,IO=0.5A,0 $^{\circ}\text{C} \leq \text{TJ} \leq +125 \,^{\circ}\text{C}$,IMAX=1.5A,PDMAX=20W,unless otherwise specified)

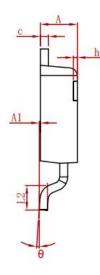
Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Line Regulation(note1)	R _{line}	T _A =25°C 3V≤V _I -V _O ≤40V		0.01	0.04	%/V
		3V≤V _I -V _O ≤40V		0.02	0.07	
Load Regulation(note1)	R _{load} -	Ta=25°C , 10mA≤ l_0 ≤ l_{MAX} V_0 <5 V V_0 \geqslant 5 V		18 0.4	25 0.5	mV
G ()	Noad -	10mA≤ l _o ≤ l _{MAX} V _O <5V V _O ≥5V	V ₀ <5V		70 1.5	%Vo
Adjustable Pin Current	ADJ	-		46	100	
Adjustable Pin Current Change	Δl _{ADJ}	3V≤V _I -V _O ≤40V 10mA≤ l _O ≤ I _{MAX} , P _D ≤ P _{MAX}		2.0	5	μΑ
Reference Voltage	V _{REF}	3V≤V _{IN} -V _O ≤40V 10mA≤ Io≤ I _{MAX} , P _D ≤ P _{MAX}	1.20	1.25	1.30	V
Temperature Stability	ST⊤	-		0.7		%/ V _O
Minimum Load Current to Maintain Regulation	I _{L(MIN)}	V _I -V _O =40V		3.5	12	mA
Maximum Output Current	lo(max)	Vi-Vo≤15V, Pd≤ Pmax Vi-Vo≤40V, Pd≤ Pmax Ta=25°C	1.0	2.2 0.3		А
RMS Noise,% of V _{OUT}	N	Ta=25°C ,10Hz≤f≤10KHz		0.003	0.01	%/ V _O
Ripple Rejection	RR	V_0 =10V, f =120Hz without C_{ADJ} C_{ADJ} =10 μ F(note2)	66	60 75		dB
Long-Term Stability,T _J =T _{HIGH}	ST	T _A =25°C for end point mesasurements, 1 0 0 0 HR		0.3	1	%
Thermal Resistance Junction to case	Reuc	-		5		°C/W

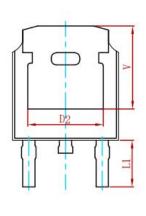


PACKAGE MECHANICAL DATA

SOT-252

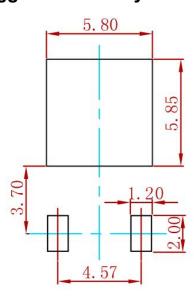






Symbol	Dimensions	In Millimeters	Dimensions	In Inches
Symbol	Min.	Max.	Min.	Max.
Α	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.635	0.770	0.025	0.030
С	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 REF.		0.190 REF.	
E	6.000	6.200	0.236	0.244
е	2.186	2.386	0.086	0.094
L	9.712	10.312	0.382	0.406
L1	2.900 REF.		0.114 REF.	
L2	1.400	1.700	0.055	0.067
L3	1.600 REF.		0.063 REF.	
L4	0.600	1.000	0.024	0.039
Ф	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.250 REF. 0.2		0.207	REF.

Suggested Pad Layout



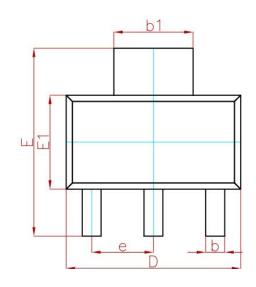
Note:

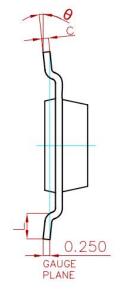
- 1. Controlling dimension:in millimeters.
- 2. General tolerance: ± 0.05 mm.
- 3. The pad layout is for reference purposes only.

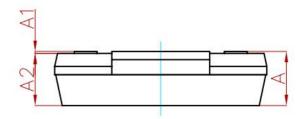


PACKAGE MECHANICAL DATA

SOT-223

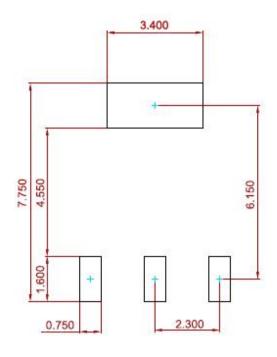






Symbol	Dimensions I	n Millimeters	Dimensions	In Inches
Cybo.	Min.	Max.	Min.	Max.
Α		1.800		0.071
A1	0.020	0.100	0.001	0.004
A2	1.500	1.700	0.059	0.067
b	0.660	0.840	0.026	0.033
b1	2.900	3.100	0.114	0.122
С	0.230	0.350	0.009	0.014
D	6.300	6.700	0.248	0.264
E	6.700	7.300	0.264	0.287
E1	3.300	3.700	0.130	0.146
е	2.300(BSC)		0.091(BSC)	
L	0.750		0.030	
θ	0°	10°	0°	10°

Suggested Pad Layout



Note:

- 1. Controlling dimension:in millimeters.
- 2. General tolerance: ± 0.05 mm.
- 3. The pad layout is for reference purposes only.



ORDERING INFORMATION

P/N	PKG	QTY
LM317MDT-MS	TO-252	2500
LM317DCYR-MS	SOT-223	2500



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